

Optically-Coupled Darlington Isolator

Optoelectronic Products

TIL 113 TIL 119

General Description

The TIL 113 and TIL 119 optical isolators are electrical and mechanical replacements for the Texas Instrument series. Optical coupling provides a high degree of ac and dc isolation. A capability for continuous operation of the input diode results in a frequency response extending to dc. Connection to the base is also provided for design flexibility.

Glassolated™

Electrically Equivalent to TI Devices

Pin-for-Pin Equivalent

Availability of Base Pin for Flexible Design

Absolute Maximum Ratings

Storage Temperature	-55°C to +150°C
Operating Temperature	-55°C to +100°C
Pin Temperature (Soldering, 10 s)	260°C
Total Package Power Dissipation at $T_A = 25^\circ\text{C}$ (LED plus Detector)	250 mW
Derate Linearly from 25°C	3.3 mW/°C

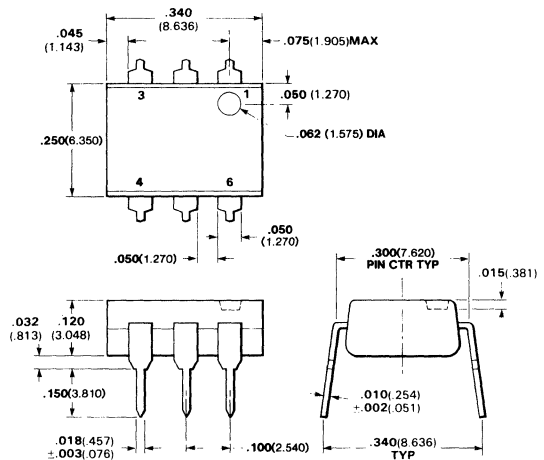
Input Diode

I_F Forward dc Current	
Continuous	100 mA
V_R Reverse Voltage	3.0 V
I_{pk} Peak Forward Current, 1 μs pulse width, 300 pps	3.0 A
P_D Power Dissipation at $T_A = 25^\circ\text{C}$	150 mW
Derate Linearly from 25°C	2.0 mW/°C

Output Transistor (Darlington)

V_{CE} Collector-to-Emitter Voltage	30 V
V_{CB} Collector-to-Base Voltage	30 V
V_{EC} Emitter-to-Collector Voltage	7.0 V
P_D Power Dissipation at $T_A = 25^\circ\text{C}$, $I_{C(max)}$ 100 mA, $V_{CE} = 1.5\text{ V}$	150 mW
Derate Linearly from 25°C	2.0 mW/°C

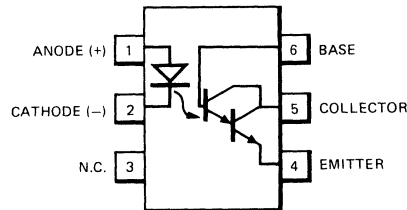
Package Outline



Notes

All dimensions in inches bold and millimeters (parentheses)
Tolerance unless specified = ± 0.015 (0.381)

Connection Diagram DIP (Top View)



Pin

1	Anode (+)	} Input Diode
2	Cathode (-)	
3	NC	
4	Emitter	} Output npn Phototransistor
5	Collector	
6	Base	

Electrical Characteristics—Input Diode $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_F	Forward Voltage			1.5	V	$I_F = 10\text{ mA}$
I_R	Reverse Current			100	μA	$V_R = 3.0\text{ V}$

Typical Electrical Characteristics

TIL 113 TIL 119

Electrical Characteristics—Output Transistor (Darlington) $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV_{CEO}	Collector-to-Emitter Breakdown Voltage	30			V	$I_C = 1.0\text{ mA}$, $I_F = 0$
BV_{CBO}	Collector-to-Base Breakdown Voltage TIL 113	30				$I_C = 10\ \mu\text{A}$, $I_F = 0$
BV_{ECO}	Emitter-to-Collector Breakdown Voltage TIL 119	7.0			V	$I_E = 10\ \mu\text{A}$, $I_F = 0$
BV_{EBO}	Emitter-to-Base Breakdown Voltage TIL 113	7.0			V	$I_E = 10\ \mu\text{A}$, $I_F = 0$
I_{CEO}	Collector-to-Emitter Leakage Current			100	nA	$V_{CE} = 10\text{ V}$, $I_F = 0$
h_{FE}	Forward Current Gain TIL 113		15 k			$V_{CE} = 1.0\text{ V}$, $I_C = 10\text{ mA}$, $I_F = \phi$

Electrical Characteristics—Coupled $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I_C	Collector Output Current (Pulsed) TIL 113	30	100		mA	$I_F = 10\text{ mA}$, $V_{CE} = 1.0\text{ V}$
	TIL 119	30	160		mA	$I_F = 10\text{ mA}$, $V_{CE} = 2.0\text{ V}$ Peak
V_{ISO}	Isolation Voltage (Note 2)	1.5 k			V	$V = 500\text{ V}$
R_{ISO}	Isolation Resistance	10^{11}			Ω	
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage TIL 113			1.0	V	$I_C = 125\text{ mA}$, $I_B = 0$, $I_F = 50\text{ mA}$
	TIL 119			1.0	V	$I_C = 10\text{ mA}$, $I_F = 10\text{ mA}$
C_{ISO}	Isolation Capacitance		1.0	1.3	pF	$V = 0$, $f = 1.0\text{ MHz}$
t_r, t_f	Rise and Fall Time (Note 1) TIL 113		300		μs	$I_C = 125\text{ mA}$, $V_{CC} = 15\text{ V}$, $R_L = 100\ \Omega$
t_r, t_f	Rise and Fall Time (Note 1) TIL 119		300		μs	$I_C = 2.5\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\ \Omega$

Notes

1. Rise time is defined as the time for the (base collector) current to rise from 10% to 90% of peak value. Fall time is defined as the time required for the current to decrease from 90% to 10% of peak value.
2. Isolation voltage defined as minimum of 5 s continuous application.